



SI7452DP-T1-GE3 Information



For Reference Only

Part Number SI7452DP-T1-GE3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 11.5A PPAK SO-8

Package PowerPAK? SO-8

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









SI7452DP-T1-GE3 Specifications

Manufacturer Part Number SI7452DP-TI-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerPAK? SO-8 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 11.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds ±20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 19.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8		
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Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4.5V @ 250μA 1.60nC @ 10V	Current - Continuous Drain (Id) @ 25°C	11.5A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case PowerPAK? SO-8 PowerPAK? SO-8	Drive Voltage (Max Rds On, Min Rds On)	10V
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Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs8.3 mOhm @ 19.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8	Gate Charge (Qg) (Max) @ Vgs	160nC @ 10V
FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 19.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Input Capacitance (Ciss) (Max) @ Vds	-
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Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Rds On (Max) @ Id, Vgs	8.3 mOhm @ 19.3A, 10V
Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case PowerPAK? SO-8	Mounting Type	Surface Mount
-	Supplier Device Package	PowerPAK? SO-8
Report errors?	Package / Case	PowerPAK? SO-8
		Report errors?

SI7452DP-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI7452DP-T1-GE3 Payment Methods



















SI7452DP-T1-GE3 Shipping Methods













If you have any question about SI7452DP-T1-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com